256Kx32 SSRAM/4Mx32 SDRAM

External Memory Solution for Texas Instruments TMS320C6000 DSP

WED9LC6816V

FEATURES

- Clock speeds:
  - SSRAM: 200, 166,150, and 133 MHz
  - SDRAMs: 125 and 100 MHz
- DSP Memory Solution
  - Texas Instruments TMS320C6201
  - Texas Instruments TMS320C6701
- Packaging:
  - 153 pin BGA, JEDEC MO-163
- 3.3V Operating supply voltage
- Direct control interface to both the SSRAM and SDRAM ports on the “C6x”
- Common address and databus
- 65% space savings vs. monolithic solution
- Reduced system inductance and capacitance

DESCRIPTION

The WED9LC6816V is a 3.3V, 256K x 32 Synchronous Pipeline SRAM and a 4Mx32 Synchronous DRAM array constructed with one 256K x 32 SBSRAM and two 4Mx16 SDRAM die mounted on a multilayer laminate substrate. The device is packaged in a 153 lead, 14mm x 22mm, BGA.

The WED9LC6816V provides a total memory solution for the Texas Instruments TMS320C6201 and the TMS320C6701 DSPs The Synchronous Pipeline SRAM is available with clock speeds of 200, 166,150 and 133 MHz, allowing the user to develop a fast external memory for the SSRAM interface port .

The SDRAM is available in clock speeds of 125 and 100 MHz, allowing the user to develop a fast external memory for the SDRAM interface port.

The WED9LC6816V is available in both commercial and industrial temperature ranges.

This product is subject to change without notice.

Figure 1 – PIN CONFIGURATION

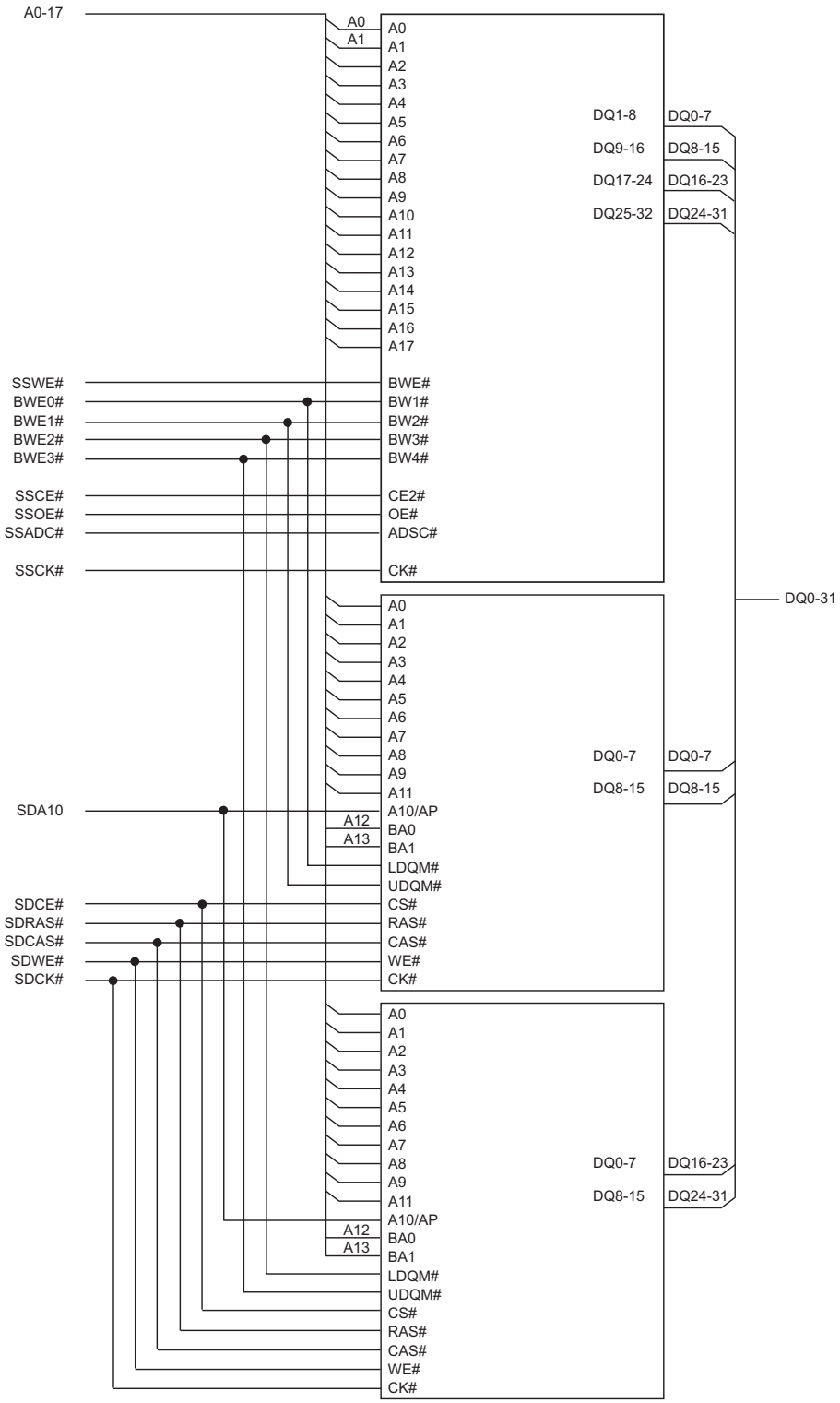
TOP VIEW

	1	2	3	4	5	6	7	8	9
A	DQ19	DQ23	V_{CC}	V_{SS}	V_{SS}	V_{SS}	V_{CC}	DQ24	DQ28
B	DQ18	DQ22	V_{CC}	V_{SS}	SDCE#	V_{SS}	V_{CC}	DQ25	DQ29
C	V_{CCQ}	V_{CCQ}	V_{CC}	SDWE#	SDA10	NC	V_{CC}	V_{CCQ}	V_{CCQ}
D	DQ17	DQ21	V_{CC}	V_{SS}	V_{SS}	V_{SS}	V_{CC}	DQ26	DQ30
E	DQ16	DQ20	V_{CC}	V_{SS}	SDCK	V_{SS}	V_{CC}	DQ27	DQ31
F	V_{CCQ}	V_{CCQ}	V_{CC}	V_{SS}	V_{SS}	V_{SS}	V_{CC}	V_{CCQ}	V_{CCQ}
G	NC	NC	NC	SDRAS#	SDCAS#	V_{SS}	A2	A4	A5
H	NC	NC	A8	V_{SS}	V_{SS}	NC	A1	A3	A10
J	A6	A7	A9	V_{SS}	V_{SS}	NC	A0	A11	A12
K	A17	NC/A18	NC/A19	V_{SS}	V_{SS}	NC	NC	A13	A14
L	NC	NC	NC	BWE2#	BWE3#	NC	NC	A15	A16
M	V_{CCQ}	V_{CCQ}	V_{CC}	BWE0#	BWE1#	NC	V_{CC}	V_{CCQ}	V_{CCQ}
N	DQ12	DQ11	V_{CC}	V_{SS}	V_{SS}	V_{SS}	V_{CC}	DQ4	DQ0
P	DQ13	DQ10	V_{CC}	V_{SS}	SSCK	V_{SS}	V_{CC}	DQ5	DQ1
R	V_{CCQ}	V_{CCQ}	V_{CC}	V_{SS}	V_{SS}	V_{SS}	V_{CC}	V_{CCQ}	V_{CCQ}
T	DQ14	DQ9	V_{CC}	SSADC#	SSWE#	NC	V_{CC}	DQ6	DQ2
U	DQ15	DQ8	V_{CC}	SSOE#	SSCE#	NC	V_{CC}	DQ7	DQ3

PIN DESCRIPTION

A0-17	Address Bus
DQ0-31	Data Bus
SSCK	SSRAM Clock
SSADC#	SSRAM Address Status Control
SSWE#	SSRAM Write Enable
SSOE#	SSRAM Output Enable
SDCK	SDRAM Clock
SDRAS#	SDRAM Row Address Strobe
SDCAS#	SDRAM Column Address Strobe
SDWE#	SDRAM Write Enable
SDA10	SDRAM Address 10/auto precharge
BWE0-3#	SSRAM Byte Write Enables SDRAM SDQM 0-3
SSCE#	Chip Enable SSRAM Device
SDCE#	Chip Enable SDRAM Device
V_{CC}	Power Supply pins
V_{CCQ}	Data Bus Power Supply pins,
V_{SS}	Ground
NC	No Contact

Figure 2 – BLOCK DIAGRAM



OUTPUT FUNCTIONAL DESCRIPTIONS

Symbol	Type	Signal	Polarity	Function
SSCK	Input	Pulse	Positive Edge	The system clock input. All of the SSRAM inputs are sampled on the rising edge of the clock.
SSADC# SSOE# SSWE#	Input	Pulse	Active Low	When sampled at the positive rising edge of the clock, SSADC#, SSOE#, and SSWE# define the operation to be executed by the SSRAM.
SSCE#	Input	Pulse	Active Low	SSCE# disable or enable SSRAM device operation.
SDCK	Input	Pulse	Positive Edge	The system clock input. All of the SDRAM inputs are sampled on the rising edge of the clock.
SDCE#	Input	Pulse	Active Low	SDCE# disable or enable device operation by masking or enabling all inputs except SDCK and BWE0
SDRAS# SDCAS# SDWE#	Input	Pulse	Active Low	When sampled at the positive rising edge of the clock, SDCAS#, SDRAS#, and SDWE# define the operation to be executed by the SDRAM.
A0-17, SDA10	Input	Level	—	Address bus for SSRAM and SDRAM A0 and A1 are the burst address inputs for the SSRAM During a Bank Active command cycle, A0-11, SDA10 defines the row address (RA0-10) when sampled at the rising clock edge. During a Read or Write command cycle, A0-7 defines the column address (CA0-7) when sampled at the rising clock edge. In addition to the row address, SDA10 is used to invoke autoprecharge operation at the end of the Burst Read or Write Cycle. If SDA10 is high, autoprecharge is selected and A12 and A13 define the bank to be precharged. If SDA10 is low, autoprecharge is disabled. During a Precharge command cycle, SDA10 is used in conjunction with A12 and A13 to control which bank(s) to precharge. If SDA10 is high, all banks will be precharged regardless of the state of A12 and A13. If SDA10 is low, then A12 and A13 are used to define which bank to precharge.
DQ0-31	Input Output	Level	—	Data Input/Output are multiplexed on the same pins.
BWE0-3#	Input	Pulse		BWE0-3# perform the byte write enable function for the SSRAM and DQM function for the SDRAM. BWE0# is associated with DQ0-7, BWE1# with DQ8-15, BWE2# with DQ16-23 and BWE3# with DQ24-31.
VCC, VSS	Supply			Power and ground for the input buffers and the core logic.
VCCQ	Supply			Data power supply pins, V_{CC} and V_{CCQ} are internally tied together

ABSOLUTE MAXIMUM RATINGS

Voltage on V_{CC} Relative to V_{SS}	-0.5V to +4.6V
V_{IN} (DQx)	-0.5V to V_{CC} +0.5V
Storage Temperature (BGA)	-55°C to +125°C
Junction Temperature	+150°C
Short Circuit Output Current	100 mA

*Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions greater than those indicated in operational sections of this specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

(0°C ≤ t_A ≤ 70°C, Commercial; -40°C ≤ t_A ≤ 85°C, Industrial)

Parameter	Symbol	Min	Max	Units
Supply Voltage (1)	V_{CC}	3.135	3.6	V
Input High Voltage (1,2)	V_{IH}	2.0	V_{CC} +0.3	V
Input Low Voltage (1,2)	V_{IL}	-0.3	0.8	V
Input Leakage Current 0 ≤ V_{IN} ≤ V_{CC}	I_{LI}	-10	10	µA
Output Leakage (Output Disabled) 0 ≤ V_{IN} ≤ V_{CC}	I_{LO}	-10	10	µA
SSRAM Output High (IOH = -4mA) (1)	V_{OH}	2.4	—	V
SSRAM Output Low (IOL = 8mA) (1)	V_{OL}	—	0.4	V
SDRAM Output High (IOH = -2mA)	V_{OH}	2.4	—	V
SDRAM Output Low (IOL = 2mA)	V_{OL}	—	0.4	V

NOTES:
1. All voltages referenced to V_{SS} (GND).
2. Overshoot: V_{IH} ≤ +6.0V for t ≤ $t_{KC}/2$
   Underershoot: V_{IL} ≤ -2.0V for t ≤ $t_{KC}/2$

DC ELECTRICAL CHARACTERISTICS

(0°C t_A ≤ 70°C, Commercial; -40°C ≤ t_A ≤ 85°C, Industrial)

Description	Conditions	Symbol	Frequency	Max	Units
Power Supply Current Operating (1,2,3)	SSRAM Active / DRAM Auto Refresh	ICC1	133MHz	625	mA
			150MHz	650	
			166MHz	700	
			200MHz	800	
Power Supply Current Operating (1,2,3)	SSRAM Active / DRAM Idle	ICC2	133MHz	425	mA
			150MHz	450	
			166MHz	495	
			200MHz	585	
Power Supply Current Operating (1,2,3)	SDRAM Active / SSRAM Idle	ICC3	83MHz	625	mA
			100MHz	650	
			125MHz	700	
CMOS Standby	SSCE# and SDCE# ≥ V_{CC} -0.2V, All other inputs at V_{IN} ≤ 0.2 or V_{IN} ≥ V_{CC} -0.2V	ISB1		40.0	mA
TTL Standby	SSCE# and SDCE# ≥ V_{IH}, All other inputs at V_{IN} ≤ V_{IL} or V_{IN} ≥ V_{IH}	ISB2		55.0	mA
Auto Refresh	SSRAM Idle / DRAM Auto Refresh	ICC5		300	mA

NOTES:
1. I_{CC} (operating) is specified with no output current. I_{CC} (operating) increases with faster cycle times and greater output loading.
2. "Device idle" means device is deselected (CE = V_{IH}) Clock is running at max frequency and Addresses are switching each cycle.
3. Typical values are measured at 3.3V, 25°C. I_{CC} (operating) is specified at specified frequency.

SSRAM AC CHARACTERISTICS

(0°C ≤ t_A ≤ 70°C, Commercial; -40°C ≤ t_A ≤ 85°C, Industrial)

Parameter	Symbol	200MHz		166MHz		150MHz		133MHz		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Clock Cycle Time	t_{KHKH}	5		6		7		8		ns
Clock HIGH Time	t_{KLKH}	1.6		2.4		2.6		2.8		ns
Clock LOW Time	t_{KHKL}	1.6		2.4		2.6		2.8		ns
Clock to output valid	t_{KHQV}		3.0		3.5		3.8		4.0	ns
Clock to output invalid	t_{KHQX}	1.5		1.5		1.5		1.5		ns
Clock to output on Low-Z	t_{KQLZ}	0		0		0		0		ns
Clock to output in High-Z	t_{KQHZ}	1.5	3	1.5	3.5	1.5	3.8	1.5	4.0	ns
Output Enable to output valid	t_{OELQV}		3.0		3.5		3.8		4.0	ns
Output Enable to output in Low-Z	t_{OELZ}	0		0		0		0		ns
Output Enable to output in High-Z	t_{OEHZ}		3.0		3.5		3.5		3.8	ns
Address, Control, Data-in Setup Time to Clock	t_S	1.5		1.5		1.5		1.5		ns
Address, Control, Data-in Hold Time to Clock	t_H	0.5		0.5		0.5		0.5		ns

SSRAM OPERATION TRUTH TABLE

Operation	Address Used	SSCE#	SSADC#	SSWE#	SSOE#	DQ
Deselected Cycle, Power Down	None	H	L	X	X	High-Z
WRITE Cycle, Begin Burst	External	L	L	L	X	D
READ Cycle, Begin Burst	External	L	L	H	L	Q
READ Cycle, Begin Burst	External	L	L	H	H	High-Z
READ Cycle, Suspend Burst	Current	X	H	H	L	Q
READ Cycle, Suspend Burst	Current	X	H	H	H	High-Z
READ Cycle, Suspend Burst	Current	H	H	H	L	Q
READ Cycle, Suspend Burst	Current	H	H	H	H	High-Z
WRITE Cycle, Suspend Burst	Current	X	H	L	X	D
WRITE Cycle, Suspend Burst	Current	H	H	L	X	D

NOTE:
1. X means “don’t care”, H means logic HIGH. L means logic LOW.
2. All inputs except SSOE# must meet setup and hold times around the rising edge (LOW to HIGH) of SSCK.
3. Suspending burst generates wait cycle
4. For a write operation following a read operation, SSOE# must be HIGH before the input data required setup time plus High-Z time for SSOE# and staying HIGH through out the input data hold time.
5. This device contains circuitry that will ensure the outputs will be in High-Z during power-up.

BGA CAPACITANCE

Description	Conditions	Symbol	Max	Units
Address Input Capacitance (1)	t_A = 25°C; f = 1MHz	CI	8	pF
Input/Output Capacitance (DQ) (1)	t_A = 25°C; f = 1MHz	CO	10	pF
Control Input Capacitance (1)	t_A = 25°C; f = 1MHz	CA	8	pF
Clock Input Capacitance (1)	t_A = 25°C; f = 1MHz	CCK	6	pF

NOTE:
1. This parameter is sampled.

SSRAM PARTIAL TRUTH TABLE

Function	SSWE#	BWE0#	BWE1#	BWE2#	BWE3#
READ	H	X	X	X	X
WRITE one Byte (DQ0-7)	L	L	H	H	H
WRITE all Bytes	L	L	L	L	L

FIGURE 3 – SSRAM READ TIMING

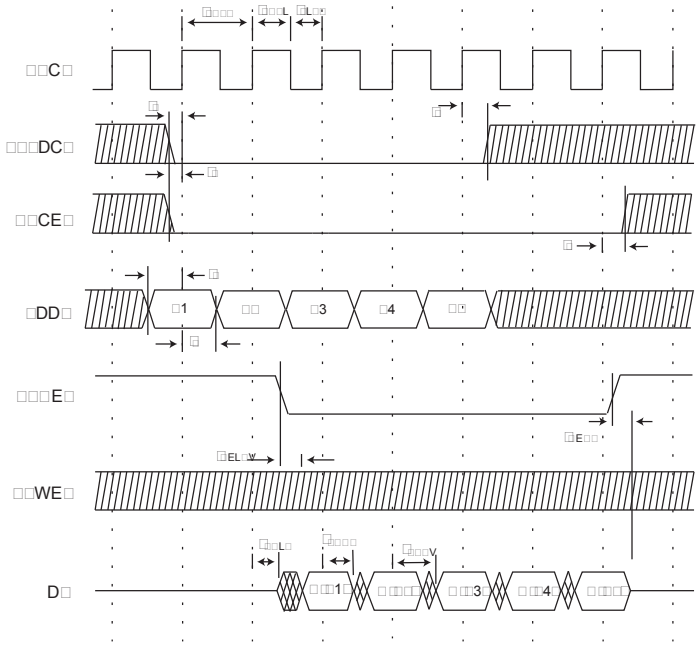
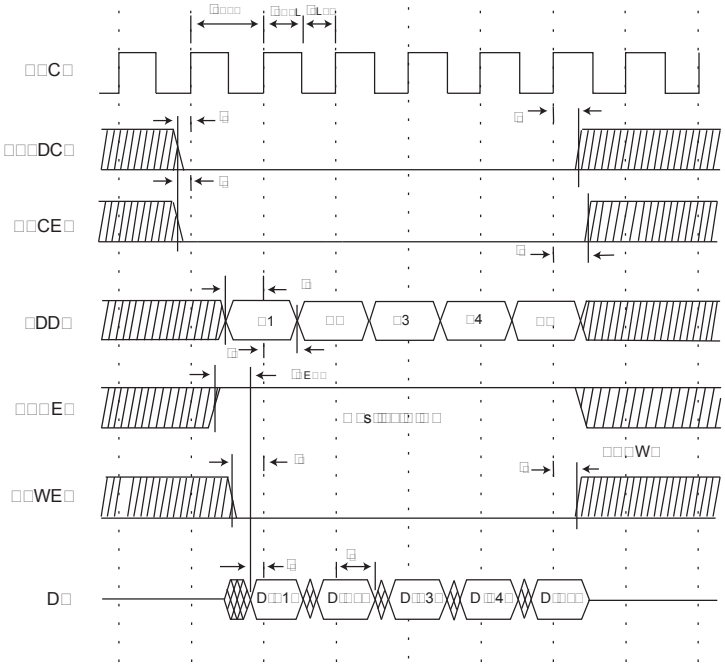


Figure 4 – SSRAM WRITE TIMING



SDRAM AC CHARACTERISTICS

(0°C ≤ t_A ≤ 70°C, Commercial; -40°C ≤ t_A ≤ 85°C, Industrial)

Parameter		Symbol	125MHz		100MHz		83MHz		Units
			Min	Max	Min	Max	Min	Max	
Clock Cycle Time (1)	CL = 3	t_{CC}	8	1000	10	1000	12	1000	ns
	CL = 2	t_{CC}	10	1000	12	1000	15	1000	ns
Clock to valid Output delay (1,2)		t_{SAC}		6		7		8	ns
Output Data Hold Time (2)		t_{OH}	3		3		3		ns
Clock HIGH Pulse Width (3)		t_{CH}	3		3		3		ns
Clock LOW Pulse Width (3)		t_{CL}	3		3		3		ns
Input Setup Time (3)		t_{SS}	2		2		2		ns
Input Hold Time (3)		t_{SH}	1		1		1		ns
CK to Output Low-Z (2)		t_{SLZ}	2		2		2		ns
CK to Output High-Z		t_{SHZ}		7		7		8	ns
Row Active to Row Active Delay (4)		t_{RRD}	20		20		24		ns
RAS\ to CAS\ Delay (4)		t_{RCD}	20		20		24		ns
Row Precharge Time (4)		t_{RP}	20		20		24		ns
Row Active Time (4)		t_{RAS}	50	10,000	50	10,000	60	10,000	ns
Row Cycle Time - Operation (4)		t_{RC}	70		80		90		ns
Row Cycle Time - Auto Refresh (4,7)		t_{RFC}	70		80		90		ns
Last Data in to New Column Address Delay (5)		t_{CDL}	1		1		1		CK
Last Data in to Row Precharge (5)		t_{RDL}	1		1		1		CK
Last Data in to Burst Stop (5)		t_{BDL}	1		1		1		CK
Column Address to Column Address Delay (6)		t_{CCD}	1		1		1		CK

NOTES:

1. Parameters depend on programmed CAS# latency.
2. If clock rise time is longer than 1ns (tRISE/2 -0.5)ns should be added to the parameter.
3. Assumed input rise and fall time = 1ns. If trise of tfall are longer than 1ns. [(tRISE = tFALL)/2] - 1ns should be added to the parameter.
4. The minimum number of clock cycles required is detemined by dividing the minimum time required by the clock cycle time and then rounding up to the next higher integer.
5. Minimum delay is required to complete write.
6. All devices allow every cycle column address changes.
7. A new command may be given t_{RFC} after self-refresh exit.

CLOCK FREQUENCY AND LATENCY PARAMETERS – 125MHz SDRAM (Unit = number of clock)

Frequency	CAS Latency	t_{RC} 70ns	t_{RAS} 50ns	t_{RP} 20ns	t_{RRD} 20ns	t_{RCD} 20ns	t_{CCD} 10ns	t_{CDL} 10ns	t_{RDL} 10ns
125MHz (8.0ns)	3	9	6	3	2	3	1	1	1
100MHz (10.0ns)	3	7	5	2	2	2	1	1	1
83MHz (12.0ns)	2	6	4	2	2	2	1	1	1

REFRESH CYCLE PARAMETERS

Parameter	Symbol	-10		-12		Units
		Min	Max	Min	Max	
Refresh Period (1,2)	t_{REF}	—	64	—	64	ms

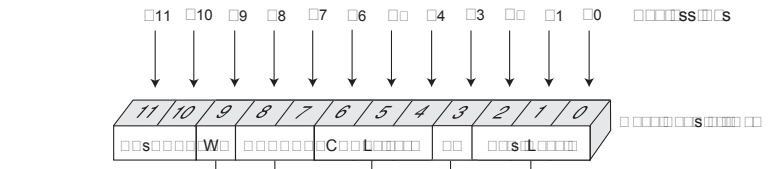
NOTES:
1. 4096 cycles
2. Any time that the Refresh Period has been exceeded, a minimum of two Auto (CBR) Refresh commands must be given to "wake-up" the device.

SDRAM COMMAND TRUTH TABLE

Function		SDCE#	SDRAS#	SDCAS#	SDWE#	BWE#	A12, A13	SDA10 A11-0	Notes
Mode Register Set		L	L	L	L	X	OP CODE		
Auto Refresh (CBR)		L	L	L	H	X	X	X	
Precharge	Single Bank	L	L	H	L	X	BA	L	2
	Precharge all Banks	L	L	H	L	X	X	H	
Bank Activate		L	L	H	H	X	BA	Row Address	2
Write		L	H	L	L	X	BA	L	2
Write with Auto Precharge		L	H	L	L	X	BA	H	2
Read		L	H	L	L	X	BA	L	2
Read with Auto Precharge		L	H	L	H	X	BA	H	2
Burst Termination		L	H	H	L	X	X	X	3
No Operation		L	H	H	H	X	X	X	
Device Deselect		H	X	X	X	X	X	X	
Data Write/Output Disable		X	X	X	X	L	X	X	4
Data Mask/Output Disable		X	X	X	X	H	X	X	4

NOTES:
1. All of the SDRAM operations are defined by states of SDCE#, SDWE#, SDRAS#, SDCAS#, and BWE $_{0\text{-}3}$ at the positive rising edge of the clock.
2. Bank Select (BA), A_{12} (BA_0) and A_{13} (BA_1) select between different banks.
3. During a Burst Write cycle there is a zero clock delay, for a Burst Read cycle the delay is equal to the CAS latency.
4. The BWE# has two functions for the data DQ Read and Write operations. During a Read cycle, when BWE# goes high at a clock timing the data outputs are disabled and become high impedance after a two clock delay. BWE# also provides a data mask function for Write cycles. When it activates, the Write operation at the clock is prohibited (zero clock latency).

MODE REGISTER SET TABLE



9	W
0	
1	

8	7	6-0	
0	0	D	
-	-	-	

3	
0	
1	

6 4	C L
0 0	
0 0 1	
0 1 0	
0 1 1	3
1 0 0	
1 0 1	
1 1 0	
1 1 1	

	L	
1 0	3 0	3 1
0 0	1	1
0 0 1		
0 1 0	4	4
0 1 1	8	8
1 0 0		
1 0 1		
1 1 0		
1 1 1		

SDRAM CURRENT STATE TRUTH TABLE

Current State	Command							Action	Notes
	SDCE#	SDRAS#	SDCAS#	SDWE#	A12 & A13 (BA)	A11-A0	Description		
Idle	L	L	L	L	OP Code		Mode Register Set	Set the Mode Register	1
	L	L	L	H	X	X	Auto or Self Refresh	Start Auto	1
	L	L	H	L	X	X	Precharge	No Operation	
	L	L	H	H	BA	Row Address	Bank Activate	Activate the specified bank and row	
	L	H	L	L	BA	Column	Write w/o Precharge	ILLEGAL	2
	L	H	L	H	BA	Column	Read w/o Precharge	ILLEGAL	1
	L	H	H	L	X	X	Burst Termination	No Operation	1
	L	H	H	H	X	X	No Operation	No Operation	
	H	X	X	X	X	X	Device Deselect	No Operation	
Row Active	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	Precharge	3
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	1
	L	H	L	L	BA	Column	Write	Start Write; Determine if Auto Precharge	4,5
	L	H	L	H	BA	Column	Read	Start Read; Determine if Auto Precharge	4,5
	L	H	H	L	X	X	Burst Termination	No Operation	
	L	H	H	H	X	X	No Operation	No Operation	
	H	X	X	X	X	X	Device Deselect	No Operation	
Read	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	Terminate Burst; Start the Precharge	
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	2
	L	H	L	L	BA	Column	Write	Terminate Burst; Start the Write cycle	5,6
	L	H	L	H	BA	Column	Read	Terminate Burst; Start a new Read cycle	5,6
	L	H	H	L	X	X	Burst Termination	Terminate the Burst	
	L	H	H	H	X	X	No Operation	Continue the Burst	
	H	X	X	X	X	X	Device Deselect	Continue the Burst	
Write	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	Terminate Burst; Start the Precharge	
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	2
	L	H	L	L	BA	Column	Write	Terminate Burst; Start a new Write cycle	5,6
	L	H	L	H	BA	Column	Read	Terminate Burst; Start the Read cycle	5,6
	L	H	H	L	X	X	Burst Termination	Terminate the Burst	
	L	H	H	H	X	X	No Operation	Continue the Burst	
	H	X	X	X	X	X	Device Deselect	Continue the Burst	

SDRAM CURRENT STATE TRUTH TABLE (cont'd)

Current State	Command							Action	Notes
	SDCE#	SDRAS#	SDCAS#	SDWE#	A12 & A13 (BA)	A11-A0	Description		
Read with Auto Precharge	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	ILLEGAL	2
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	2
	L	H	L	L	BA	Column	Write	ILLEGAL	
	L	H	L	H	BA	Column	Read	ILLEGAL	
	L	H	H	L	X	X	Burst Termination	ILLEGAL	
	L	H	H	H	X	X	No Operation	Continue the Burst	
	H	X	X	X	X	X	Device Deselect	Continue the Burst	
Write with Auto Precharge	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	ILLEGAL	2
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	2
	L	H	L	L	BA	Column	Write	ILLEGAL	
	L	H	L	H	BA	Column	Read	ILLEGAL	
	L	H	H	L	X	X	Burst Termination	ILLEGAL	
	L	H	H	H	X	X	No Operation	Continue the Burst	
	H	X	X	X	X	X	Device Deselect	Continue the Burst	
Precharging	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	No Operation; Bank(s) idle after t_{RP}	
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	2
	L	H	L	L	BA	Column	Write w/o Precharge	ILLEGAL	2
	L	H	L	H	BA	Column	Read w/o Precharge	ILLEGAL	20
	L	H	H	L	X	X	Burst Termination	No Operation; Bank(s) idle after t_{RP}	
	L	H	H	H	X	X	No Operation	No Operation; Bank(s) idle after t_{RP}	
	H	X	X	X	X	X	Device Deselect	No Operation; Bank(s) idle after t_{RP}	
Row Activating	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	ILLEGAL	2
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	2
	L	H	L	L	BA	Column	Write	ILLEGAL	2
	L	H	L	H	BA	Column	Read	ILLEGAL	2
	L	H	H	L	X	X	Burst Termination	No Operation; Row active after t_{RCD}	
	L	H	H	H	X	X	No Operation	No Operation; Row active after t_{RCD}	
	H	X	X	X	X	X	Device Deselect	No Operation; Row active after t_{RCD}	

SDRAM Current State Truth Table (cont'd)

Current State	Command							Action	Notes
	SDCE#	SDRAS#	SDCAS#	SDWE#	A12 & A13 (BA)	A11-A0	Description		
Write Recovering	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto orSelf Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	ILLEGAL	2
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	2
	L	H	L	L	BA	Column	Write	Start Write; Determine if Auto Precharge	6
	L	H	L	H	BA	Column	Read	Start Read; Determine if Auto Precharge	6
	L	H	H	L	X	X	Burst Termination	No Operation; Row active after t_{DPL}	
	L	H	H	H	X	X	No Operation	No Operation; Row active after t_{DPL}	
	H	X	X	X	X	X	Device Deselect	No Operation; Row active after t_{DPL}	
Write Recovering with Auto Precharge	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto orSelf Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	ILLEGAL	2
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	2
	L	H	L	L	BA	Column	Write	ILLEGAL	2,6
	L	H	L	H	BA	Column	Read	ILLEGAL	2,6
	L	H	H	L	X	X	Burst Termination	No Operation; Precharge after t_{DPL}	
	L	H	H	H	X	X	No Operation	No Operation; Precharge after t_{DPL}	
	H	X	X	X	X	X	Device Deselect	No Operation; Precharge after t_{DPL}	
Refreshing	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	ILLEGAL	
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	
	L	H	L	L	BA	Column	Write	ILLEGAL	
	L	H	L	H	BA	Column	Read	ILLEGAL	
	L	H	H	L	X	X	Burst Termination	No Operation; Idle after t_{RC}	
	L	H	H	H	X	X	No Operation	No Operation; Idle after t_{RC}	
	H	X	X	X	X	X	Device Deselect	No Operation; Idle after t_{RC}	
Mode Register Accessing	L	L	L	L	OP Code		Mode Register Set	ILLEGAL	
	L	L	L	H	X	X	Auto or Self Refresh	ILLEGAL	
	L	L	H	L	X	X	Precharge	ILLEGAL	
	L	L	H	H	BA	Row Address	Bank Activate	ILLEGAL	
	L	H	L	L	BA	Column	Write	ILLEGAL	
	L	H	L	H	BA	Column	Read	ILLEGAL	
	L	H	H	L	X	X	Burst Termination	ILLEGAL	
	L	H	H	H	X	X	No Operation	No Operation; Idle after two clock cycles	
	H	X	X	X	X	X	Device Deselect	No Operation; Idle after two clock cycles	

NOTES:

1. Both Banks must be idle otherwise it is an illegal action.
2. The Current State refers only refers to one of the banks, if BA selects this bank then the action is illegal. If BA selects the bank not being referenced by the Current State then the action may be legal depending on the state of that bank.
3. The minimum and maximum Active time (t_{RAS}) must be satisfied.
4. The RAS# to CAS# Delay (t_{RCD}) must occur before the command is given.
5. Address SDA10 is used to determine if the Auto Precharge function is activated.
6. The command must satisfy any bus contention, bus turn around, and/or write recovery requirements. The command is illegal if the minimum bank to bank delay time (t_{RRD}) is not satisfied.

Figure 5 – SDRAM SINGLE BIT READ-WRITE-READ CYCLE (SAME PAGE) @ CAS LATENCY = 3, BURST LENGTH = 1

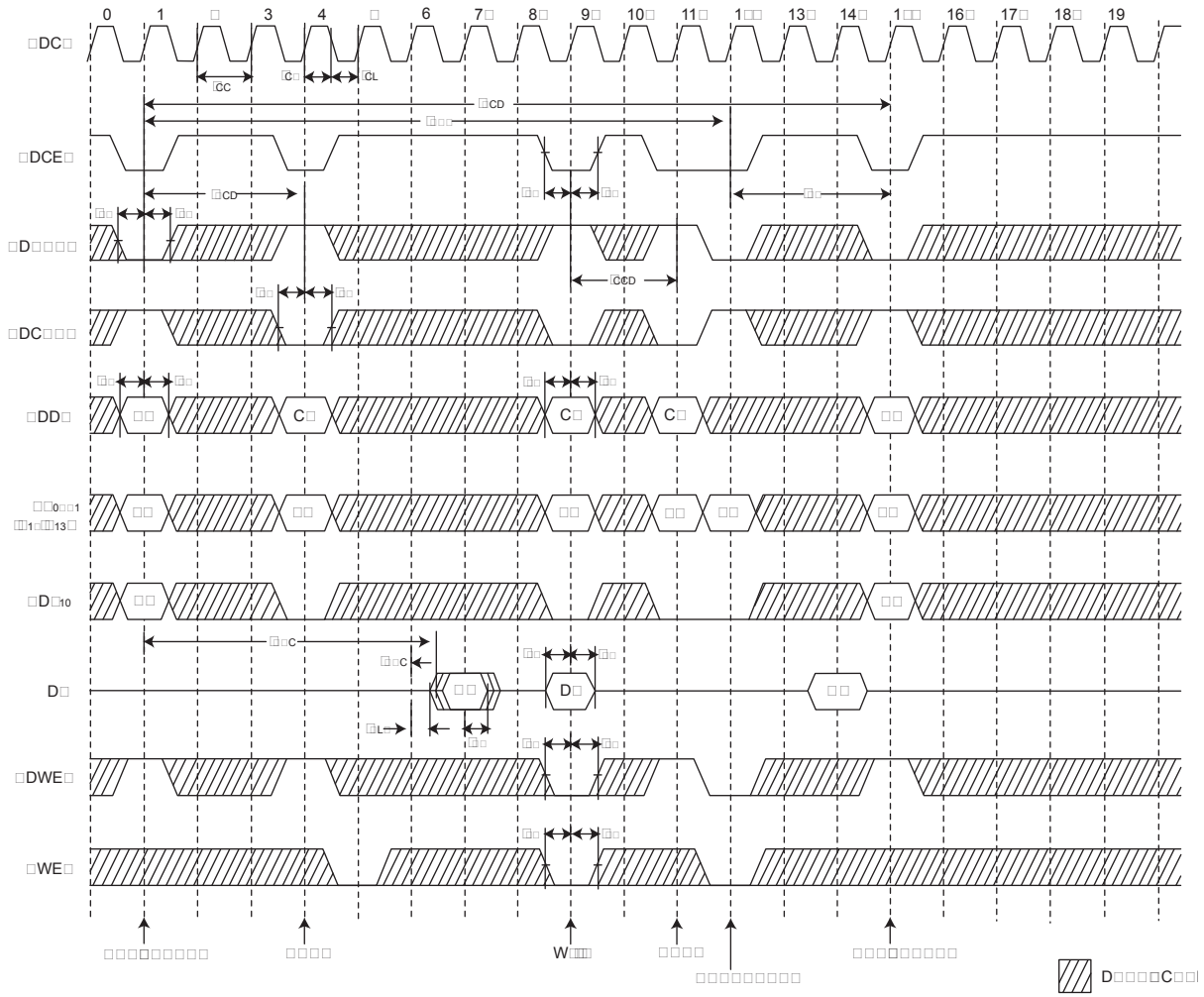


Figure 6 – SDRAM POWER UP SEQUENCE

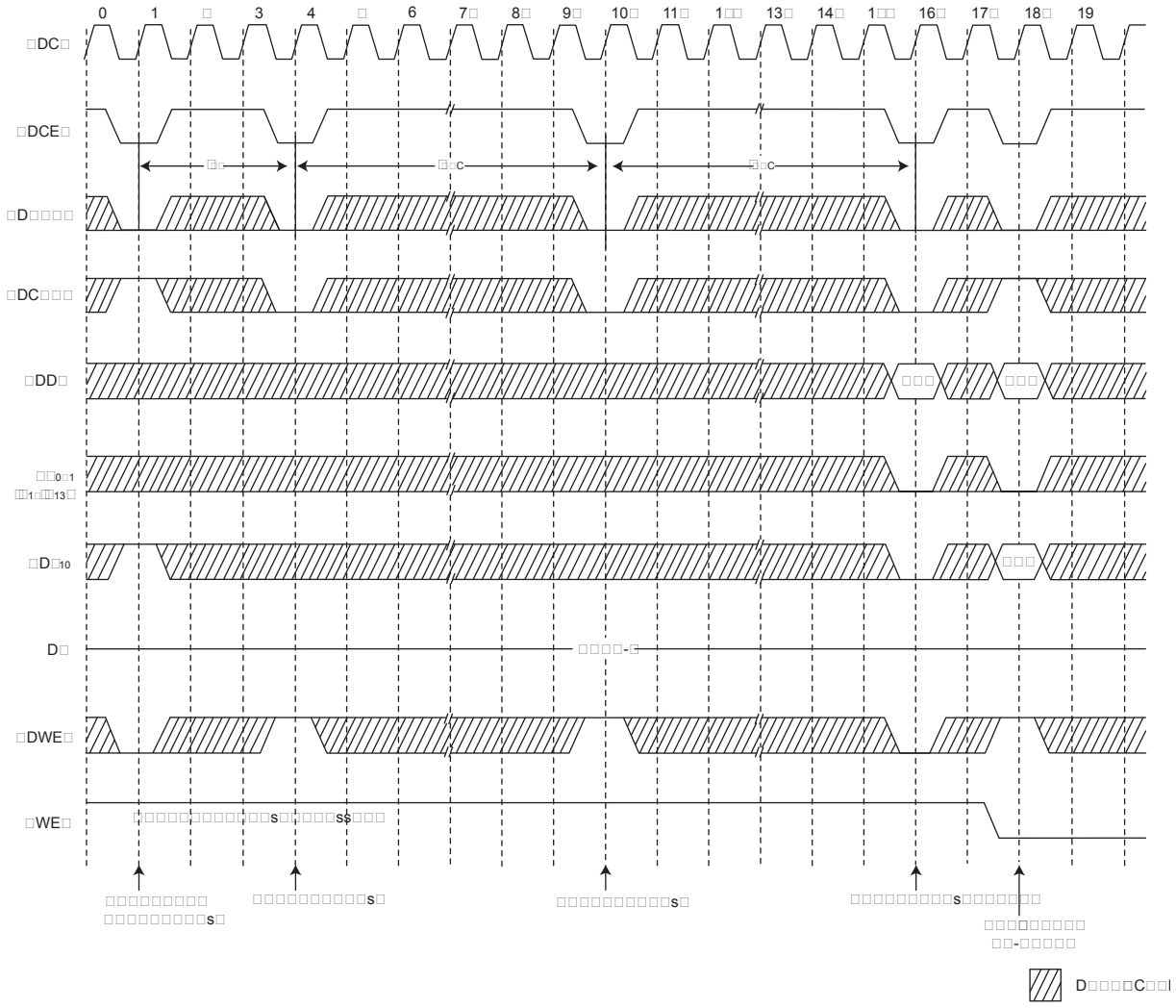
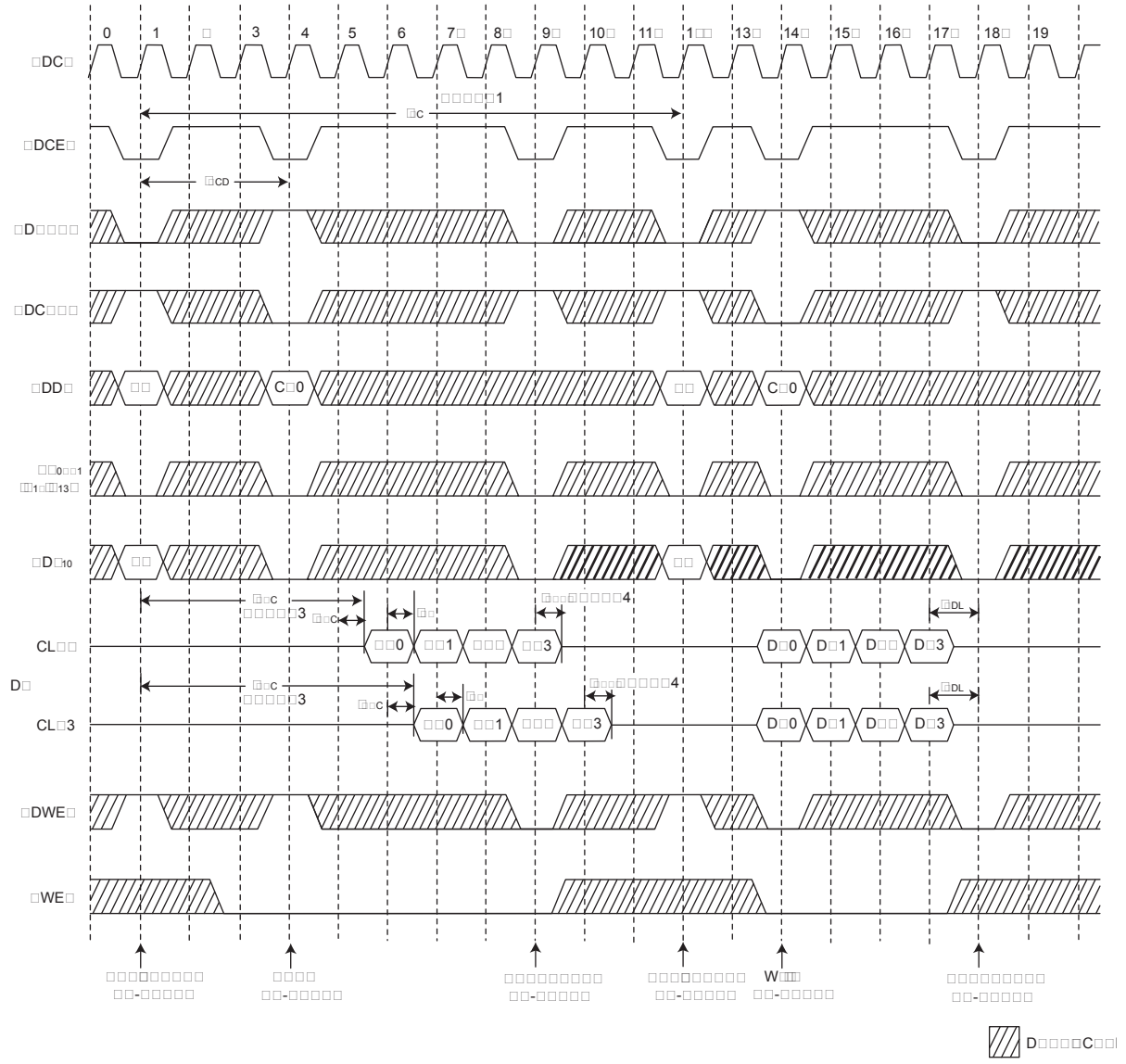


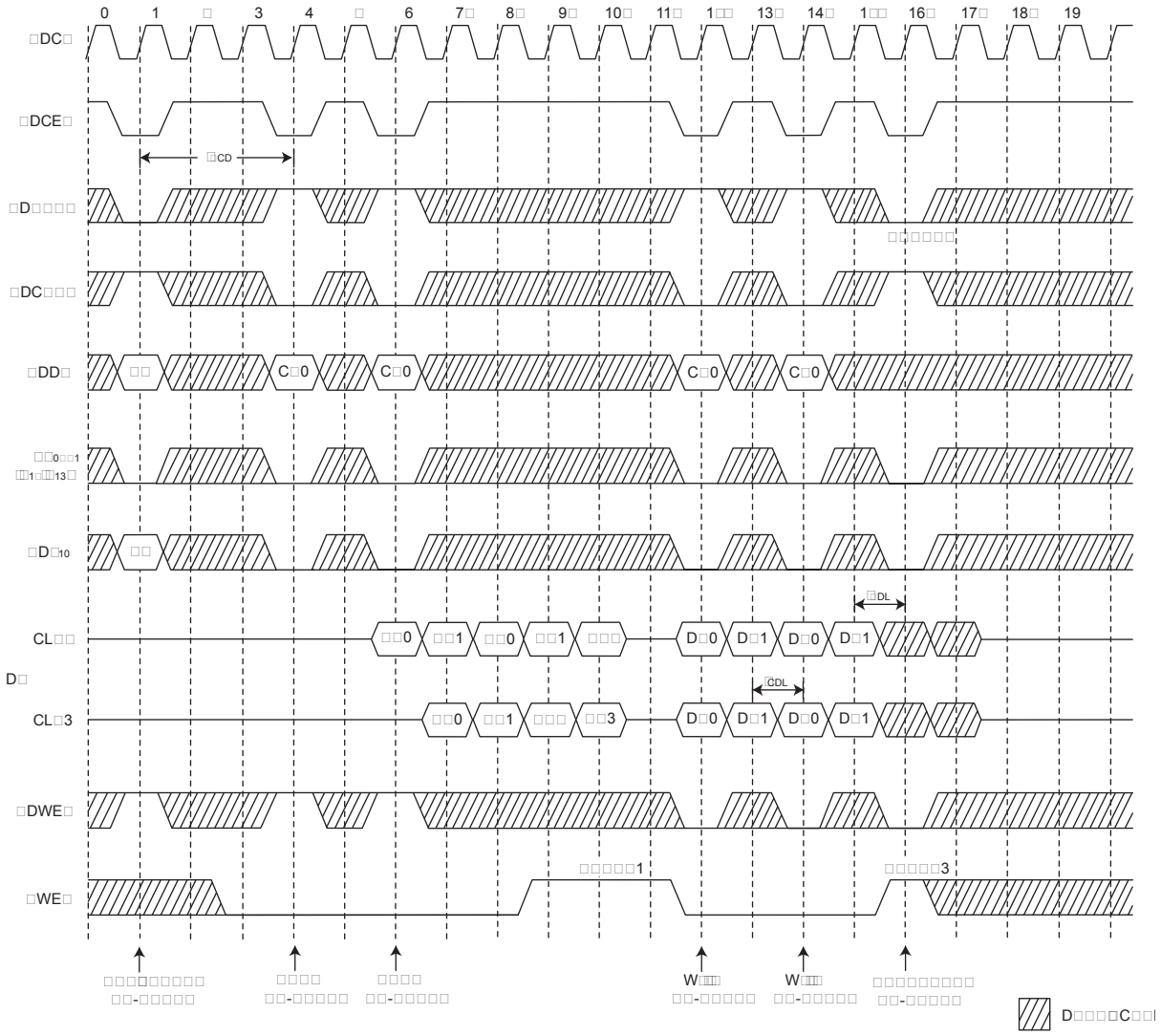
Figure 7 – SDRAM READ & WRITE CYCLE AT SAME BANK @ BURST LENGTH = 4



NOTES:

1. Minimum row cycle times are required to complete internal DRAM operation.
2. Row precharge can interrupt burst on any cycle. (CAS Latency - 1) number of valid output data is available after Row precharge. Last valid output will be Hi-Z (t_{SHZ}) after the clock.
3. Access time from Row active command. t_{CC} *(t_{RCD} + CAS Latency - 1) + t_{SAC}.
4. Output will be Hi-Z after the end of burst. (1, 2, 4, 8 & Full page bit burst)

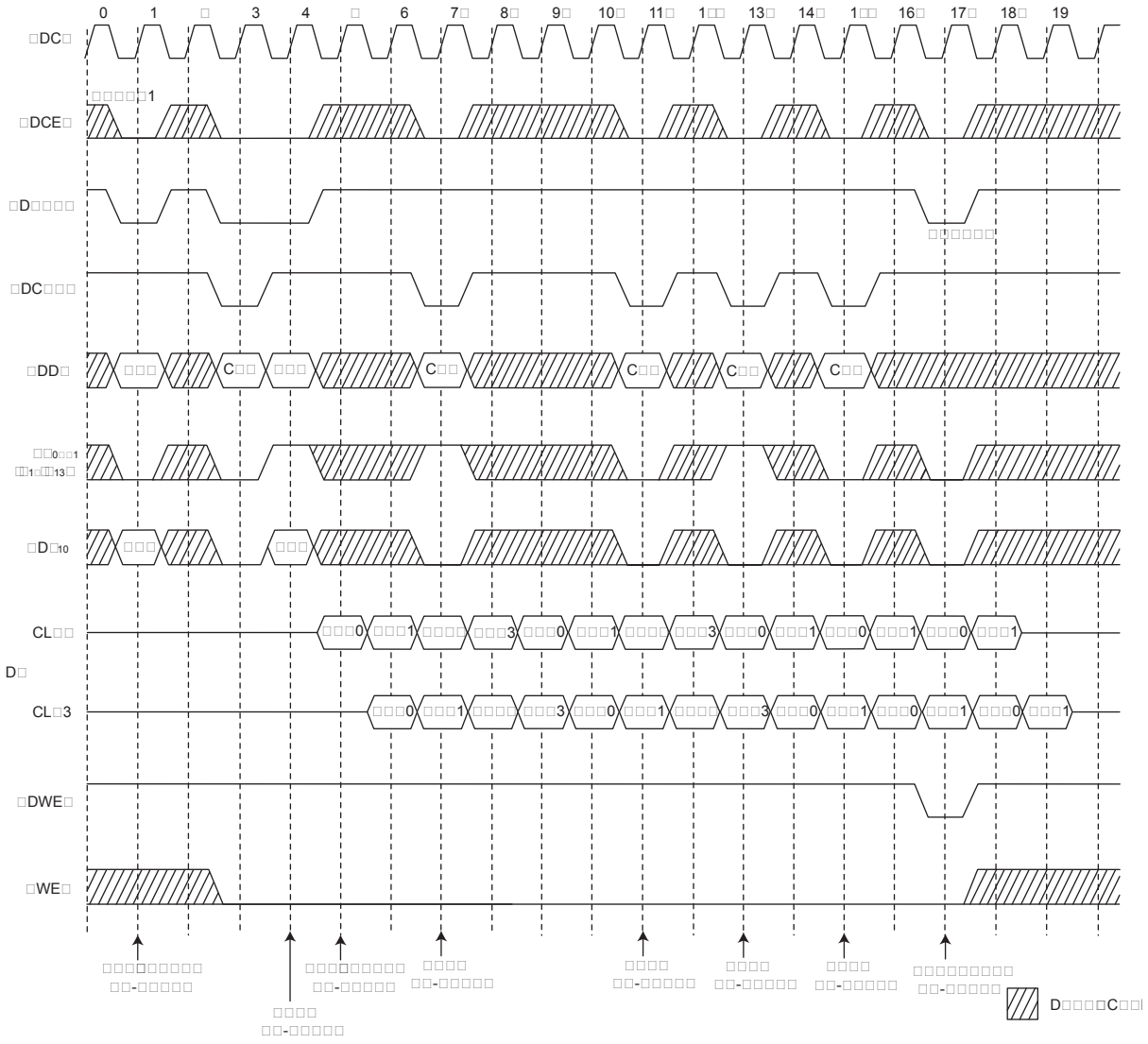
Figure 8 – SDRAM PAGE READ & WRITE CYCLE AT SAME BANK @ BURST LENGTH = 4



NOTES:

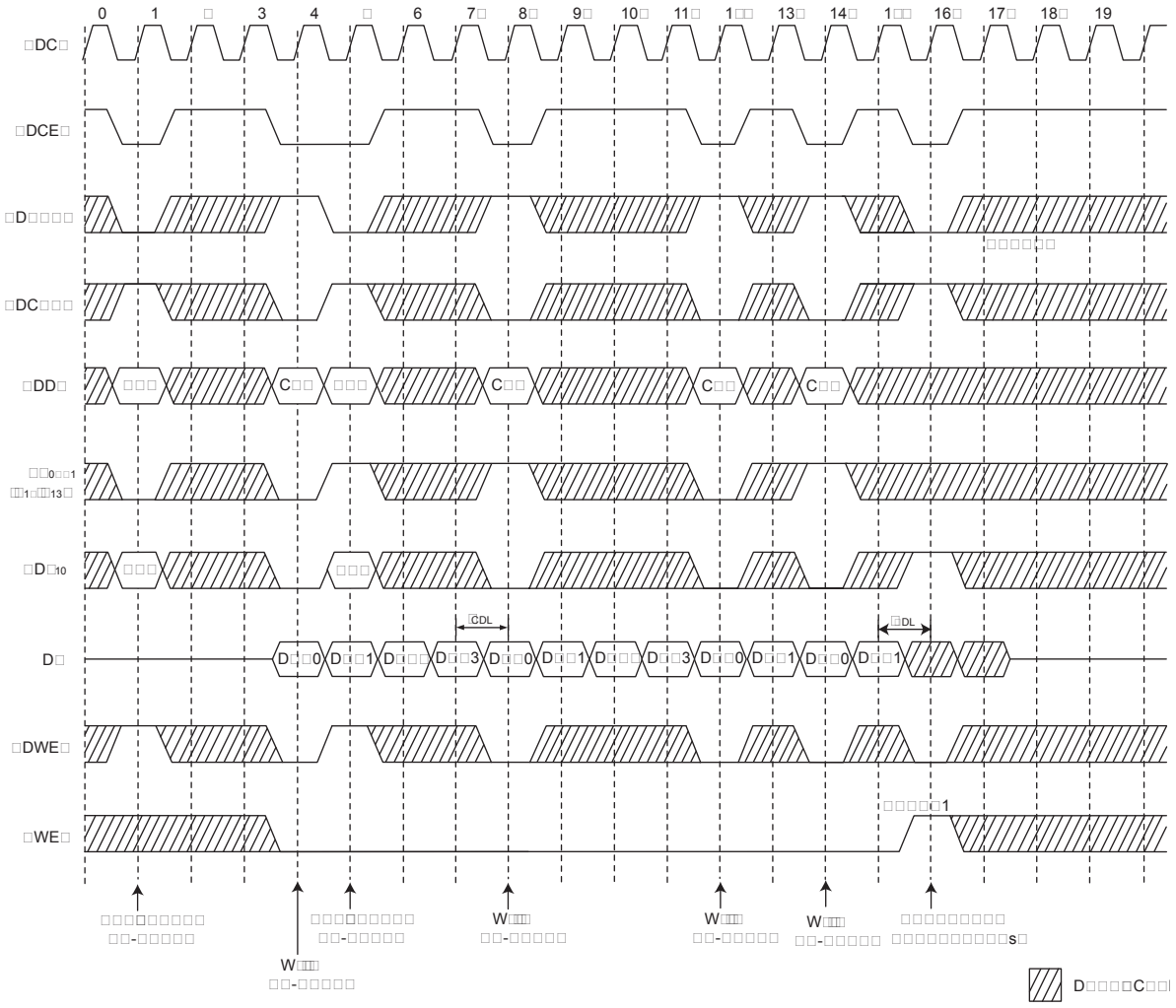
1. To write data before burst read ends. BWE# should be asserted three cycle prior to write command to avoid bus contention.
2. Row precharge will interrupt writing. Last data input, t_{RDL} before Row precharge will be written.
3. BWE# should mask invalid input data on precharge command cycle when asserting precharge before end of burst. Input data after Row precharge cycle will be masked internally.

Figure 9 – SDRAM PAGE READ CYCLE AT DIFFERENT BANK @ BURST LENGTH = 4



NOTES:
1. SDCE# can be “don’t care” when SDRAS#, SDCAS# and SDWE# are high at the clock going high edge.
2. To interrupt a burst read by Row precharge, both the read and the precharge banks must be the same.

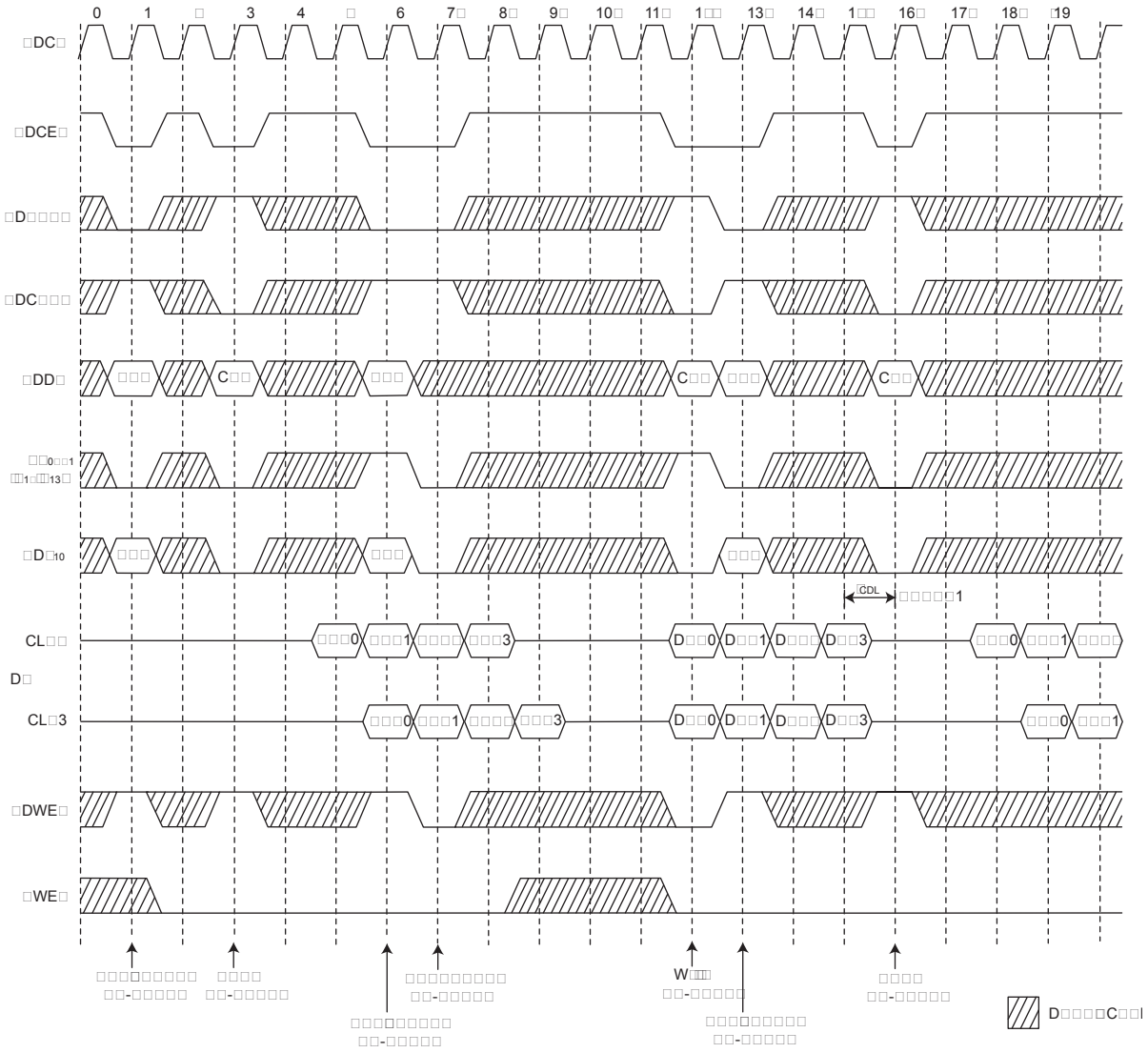
Figure 10 – SDRAM PAGE WRITE CYCLE AT DIFFERENT BANK @ BURST LENGTH = 4



NOTES:

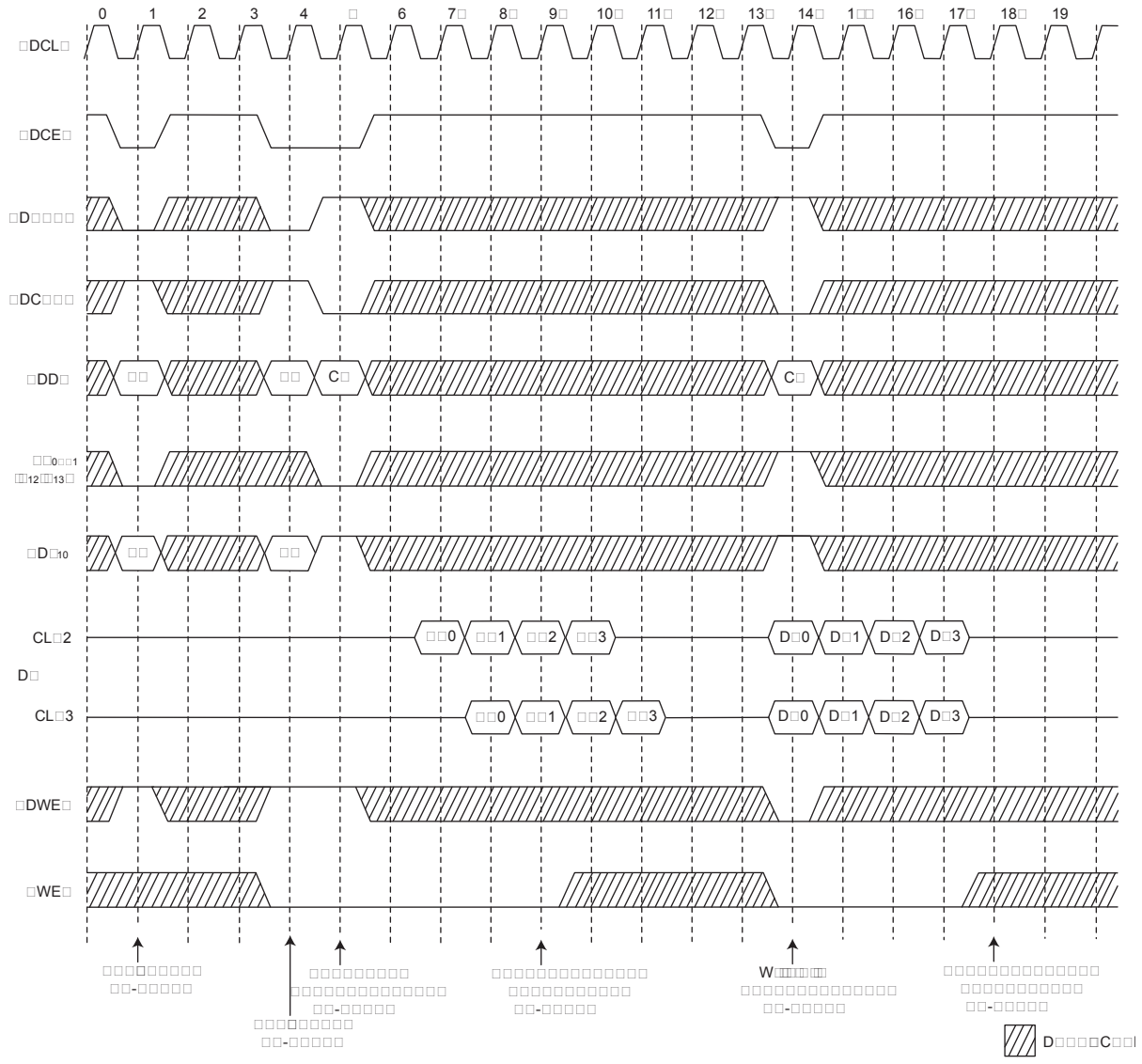
1. To interrupt burst write by Row precharge, BWE# should be asserted to mask invalid input data.
2. To interrupt a burst read by Row precharge, both the read and the precharge banks must be the same.

Figure 11 – SDRAM READ & WRITE CYCLE AT DIFFERENT BANK @ BURST LENGTH = 4



NOTES:
1. t_{CDL} should be met to complete write.

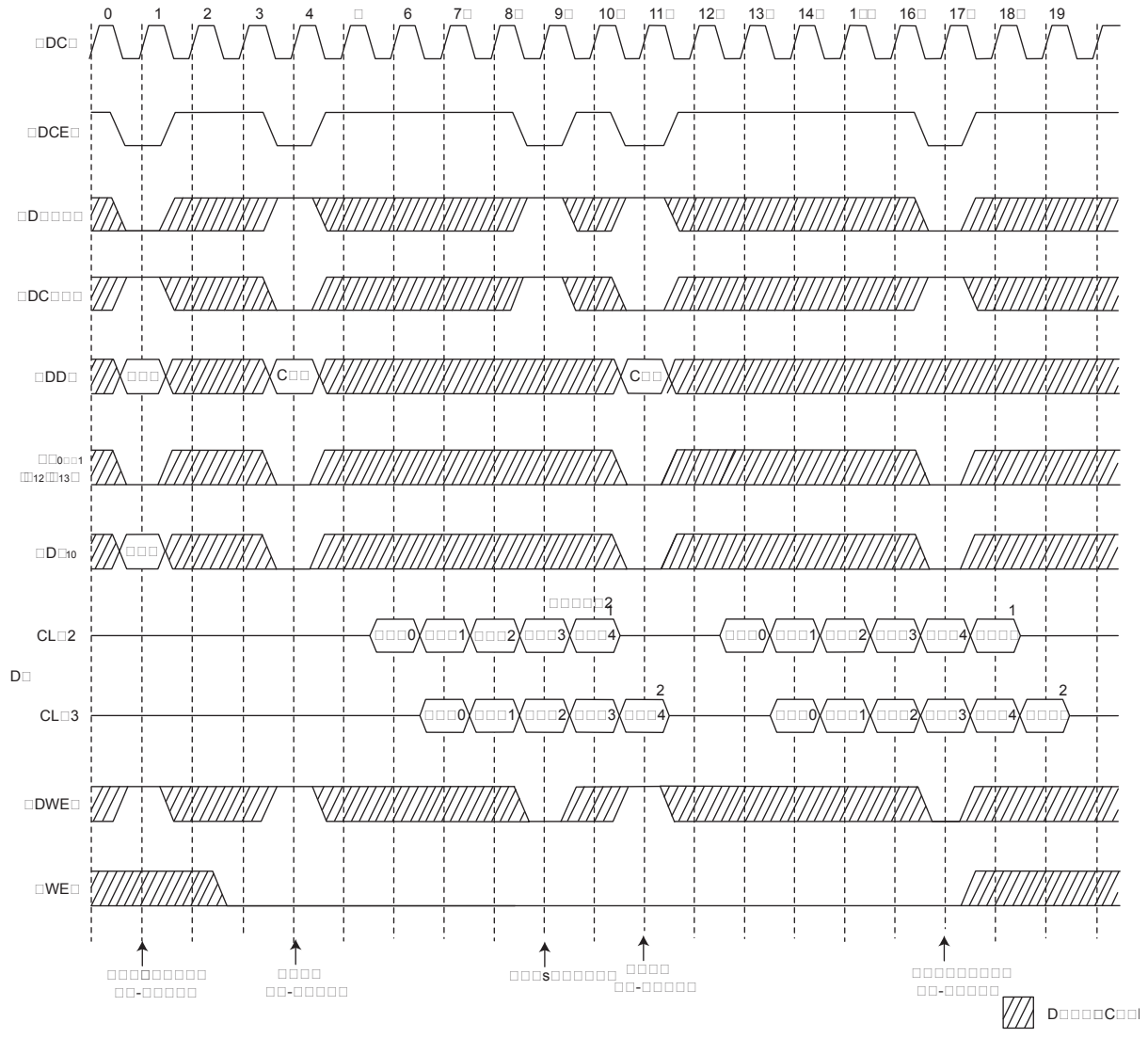
Figure 12 – SDRAM READ & WRITE CYCLE WITH AUTO PRECHARGE @ BURST LENGTH = 4



NOTES:

1. t_{CDL} should be controlled to meet minimum t_{RAS} before internal precharge start. (In the case of Burst Length = 1 & 2 and BRSW mode)

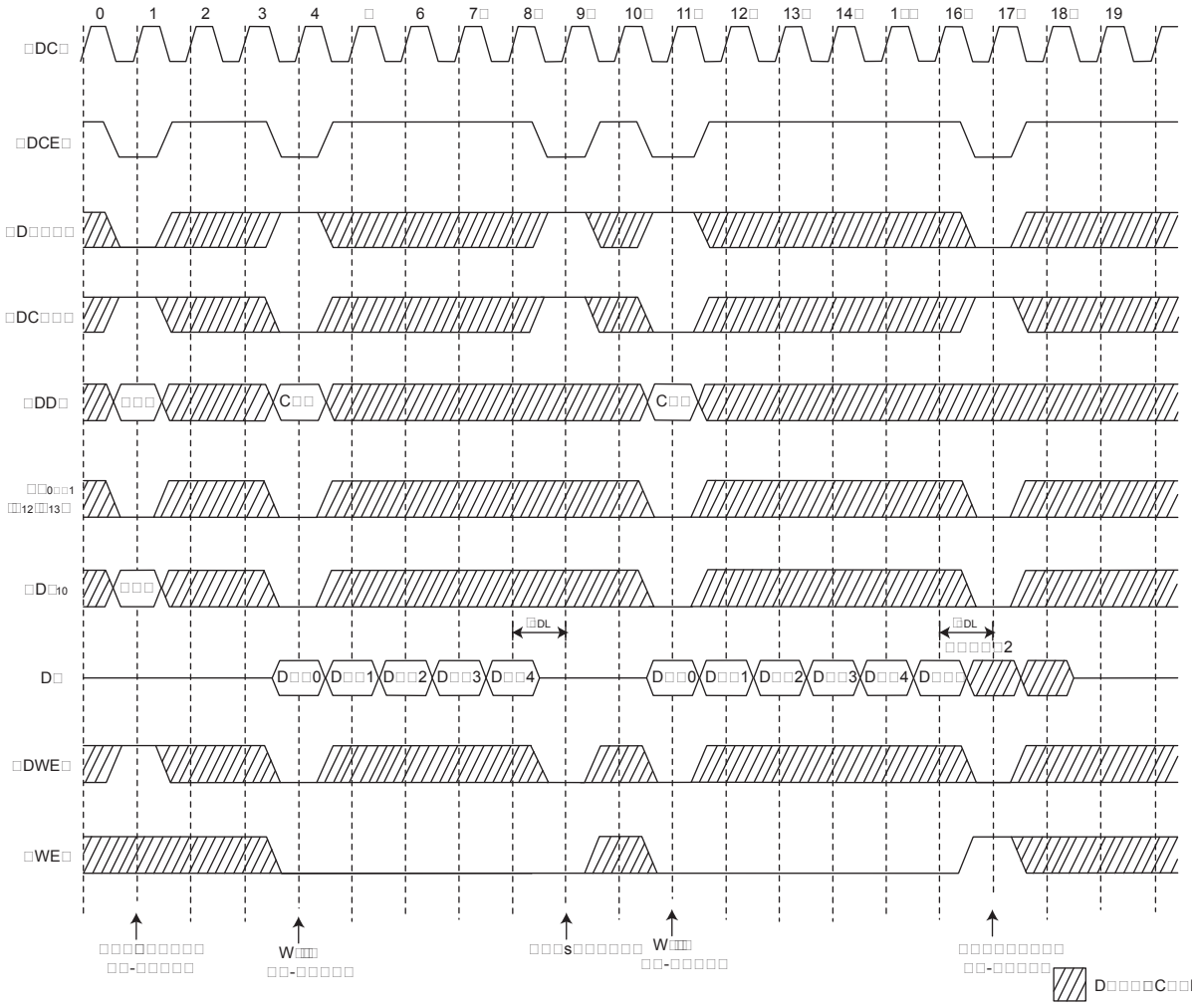
Figure 13 – SDRAM READ INTERRUPTED BY PRECHARGE COMMAND & READ BURST STOP @ BURST LENGTH = FULL PAGE



NOTES:

1. At full page mode, burst is end at the end of burst. So auto precharge is possible.
2. About the valid DQs after burst stop, it is the same as the case of SDRAS# interrupt. Both cases are illustrated in the above timing diagram. See the label 1, 2 on each of them. But at burst write, burst stop and SDRAS# interrupt should be compared carefully. Refer to the timing diagram of “Full page write burst stop cycle”.
3. Burst stop is valid at every burst length.

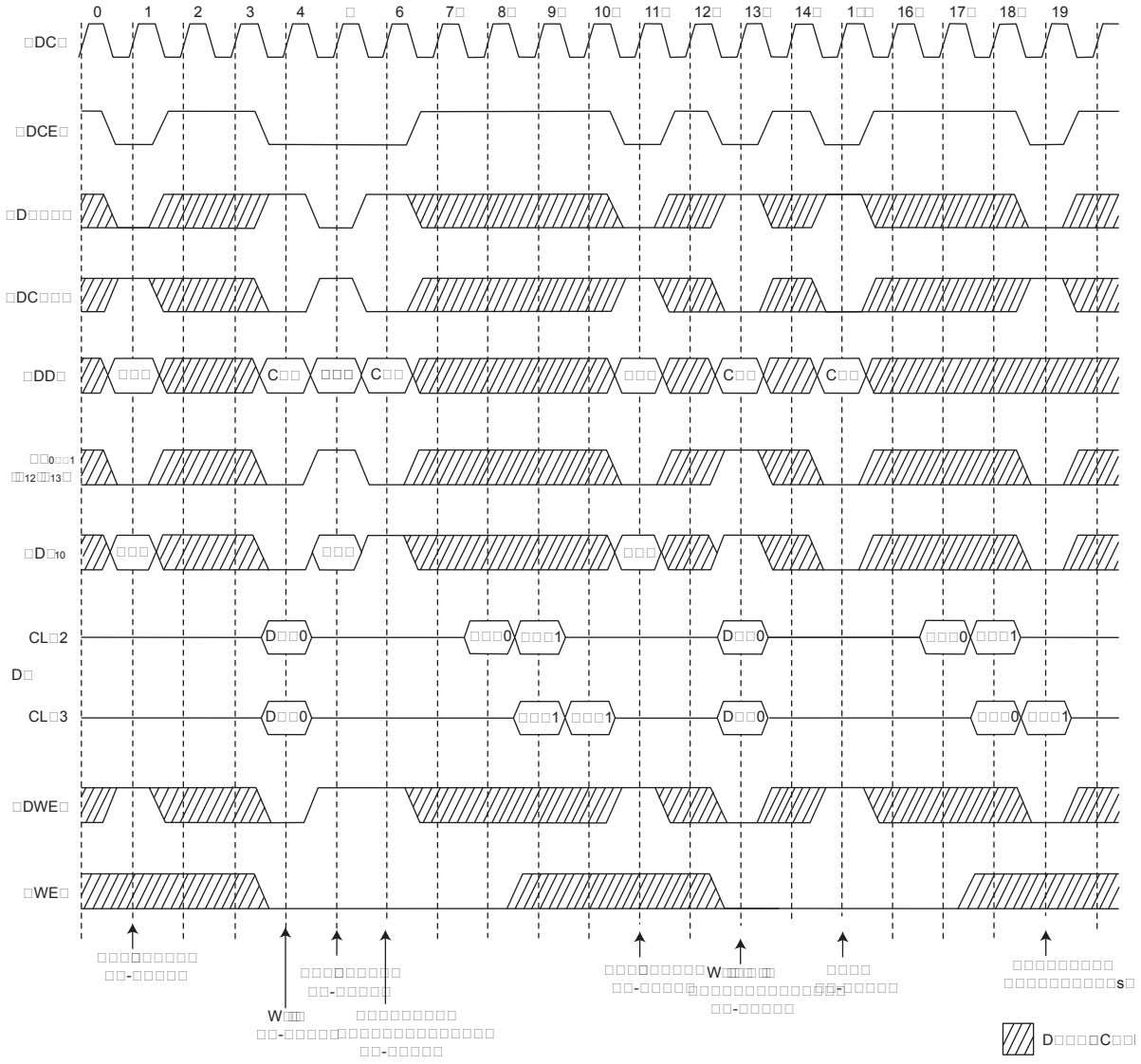
Figure 14 – SDRAM WRITE INTERRUPTED BY PRECHARGE COMMAND & WRITE BURST STOP @ BURST LENGTH = FULL PAGE



NOTES:

1. At full page mode, burst is end at the end of burst. So auto precharge is possible.
2. Data-in at the cycle of interrupted by precharge can not be written into the corresponding memory cell. It is defined by AC parameter of t_{RDL}. BWE# at write interrupt by precharge command is needed to prevent invalid write.
   BWE# should mask invalid input data on precharge command cycle when asserting precharge before end of burst. Input data after Row recharge cycle will be masked internally.
3. Burst stop is valid at every burst length.

Figure 15 – SDRAM BURST READ SINGLE BIT WRITE CYCLE @ BURST LENGTH = 2

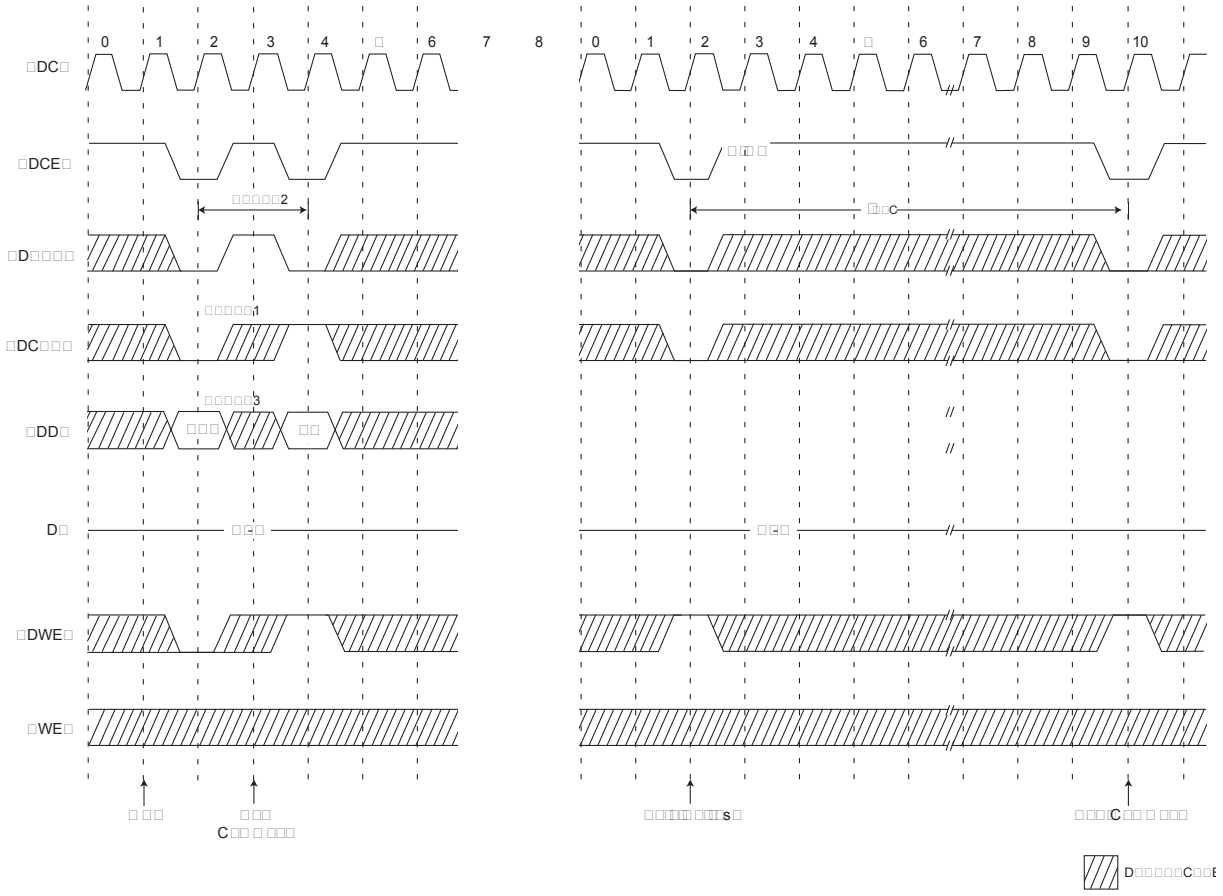


NOTES:

1. BRSW modes enabled by setting A9 "High" at MRS (Mode Register Set).
   At the BRSW Mode, the burst length at Write is fixed to "1" regardless of programmed burst length.
2. When BRSW write command with auto precharge is executed, keep it in mind that t_{RAS} should not be violated. Auto precharge is executed at the burst-end cycle, so in the case of BRSW write command, the next cycle starts the precharge.

Figure 16 –

SDRAM MODE REGISTER SET CYCLE **SDRAM AUTO REFRESH CYCLE**

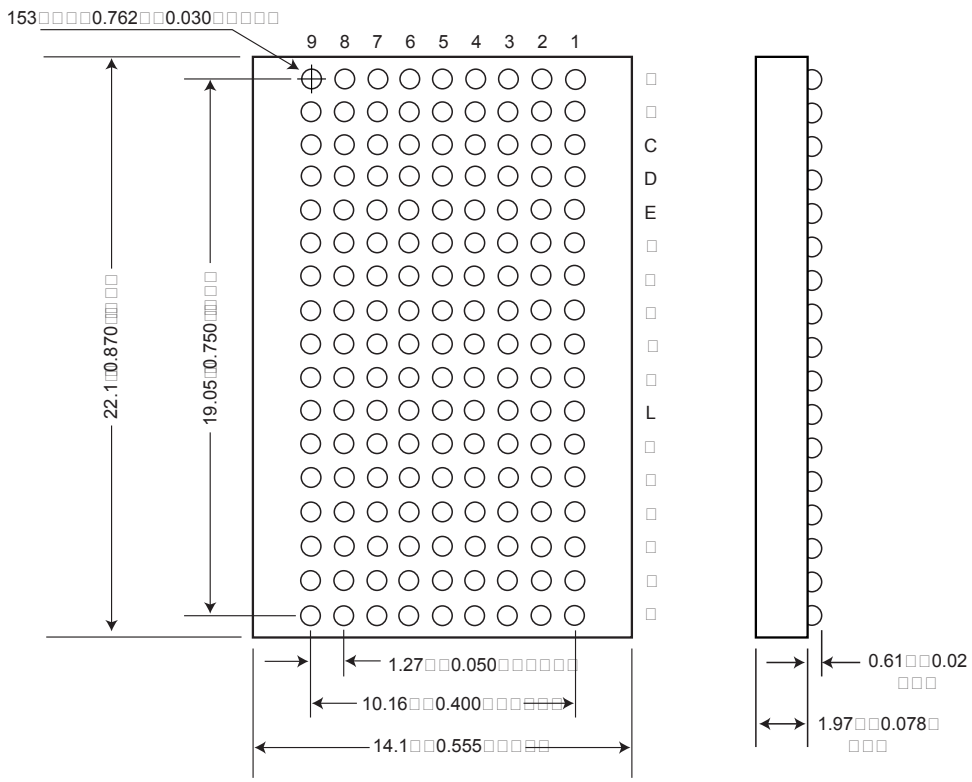


*Both banks precharge should be completed before Mode Register Set cycle and Auto refresh cycle.

NOTES:
MODE REGISTER SET CYCLE

1. SDCE#, SDRAS#, SDCAS# & SDWE# activation at the same clock cycle with address key will set internal mode register.
2. Minimum 2 clock cycles should be met before new SDRAS# activation.
3. Please refer to Mode Register Set Table.

PACKAGE DESCRIPTION: 153 LEAD BGA (17 X 9 BALL ARRAY) JEDEC MP-163



NOTE:
Ball attach pad for above BGA package is 480 microns in diameter. Pad is solder mask defined.

ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

Ordering Information

Commercial (0°C ≤ TA ≤ 70°C)

Part Number	SSRAM Access	SDRAM Access
WED9LC6816V2012BC	200MHz	125MHz
WED9LC6816V2010BC	200MHz	100MHz
WED9LC6816V1612BC	166MHz	125MHz
WED9LC6816V1610BC	166MHz	100MHz
WED9LC6816V1512BC	150MHz	125MHz
WED9LC6816V1510BC	150MHz	100MHz
WED9LC6816V1312BC	133MHz	125MHz
WED9LC6816V1310BC	133MHz	100MHz

Industrial (-40°C ≤ TA ≤ 85°C)

Part Number	SSRAM Access	SDRAM Access
WED9LC6816V2012BI	200MHz	125MHz
WED9LC6816V2010BI	200MHz	100MHz
WED9LC6816V1612BI	166MHz	125MHz
WED9LC6816V1610BI	166MHz	100MHz
WED9LC6816V1512BI	150MHz	125MHz
WED9LC6816V1510BI	150MHz	100MHz
WED9LC6816V1312BI	133MHz	125MHz
WED9LC6816V1310BI	133MHz	100MHz

Document Title

256Kx32 SSRAM/4Mx32 SDRAM – External Memory Solution for Texas Instruments TMS320C6000 DSP

Revision History

Rev #	History	Release Date	Status
Rev 2	Changes (Pg. 1, 26) 2.1 Corrected pinout – Row C missing - added, B4 - VSS, B5 - SDCE# 2.2 Corrected MO drawing	July 2010	Final
Rev 3	Changes (Pg. 2, 4, 5, 8) 3.1 Add A17 to Figure 2 – Block Diagram 3.2 Correct DC electrical characteristics: a) Remove TYP Values b) Add SDRAM to conditions for power supply current operations c) Add SSRAM idle / DRAM auto refresh to auto refresh d) Update COMS and TTL standby conditions 3.3 Change SSRAM AC characteristics: a) Clock to output valid from 2.5 max to 3.0 max @ 200MHz b) Output enable to output valid from 2.5 max to 3.0 max @ 200MHz 3.4 Remove clock frequency and latency parameters – 100MHz DRAM 3.5 Change column address to column address delay to 1 versus 1.5 3.6 Remove number of valid output data	February 2013	Final
Rev 4	Changes (Pg. All) (ECN 10156) 4.1 Change document layout from Microsemi to Mercury Systems	August 2016	Final

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